

09/845.231

F0630

SPECIFICATION

The specification is objected to because of a grammatical informality on page 2, line 6. It is submitted that this objection should be withdrawn for at least the following reason. The specification has been amended herein at page 2, line 6 to cure the informality. Please replace the entire third paragraph under the heading "Background" beginning at page 1, line 26 and ending on page 2, line 9 with the following:

ad  
Several techniques for depositing thin films are known in the art. One exemplary technique for depositing a thin film is *via* chemical vapor deposition (CVD), wherein a wafer is introduced into a process chamber, heated to a desired temperature and gases are flown to initiate the deposition process. As in many conventional thin film deposition techniques, this CVD process inevitably permits the introduction of impurities into the deposited thin film layer. In CVD, a combination of inert carrier gasses and reactant gasses are introduced into the chamber wherein the elevated wafer temperature causes the reactive gasses to break down on the wafer surface thereby depositing the desired thin film on the wafer surface. To maintain the desired chemical reaction, the desired temperature in the chamber and at the wafer surface must be maintained. Accordingly, the wafer may be in continuous and direct contact with a means for heating the wafer. The means for heating the wafer (e.g. ceramic, quartz or metal susceptor) may release impurities into the deposition chamber, which impurities may be deposited in the thin film layer. Conductive impurities can negatively impact the manufactured chip by, for example, producing electrical shorts, while non-conducting impurities can negatively impact the manufactured chip by, for example, increasing the resistance of conductive layers.